

<b>Notice of References Cited</b>	Application/Control No. 10/573,458		Applicant(s)/Patent Under Reexamination OTSUKA ET AL.	
	Examiner Christopher M. Roland		Art Unit 2893	Page 1 of 2

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2006/0006413	01-2006	Beach, Robert	257/192
*	B	US-2006/0108659	05-2006	Yanagihara et al.	257/471
*	C	US-5,099,295	03-1992	Ogawa, Masamichi	257/24
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Peatman, W. C. B. et al. "A Novel Schottky/2-DEG Diode for Millimeter- and Submillimeter-Wave Multiplier Applications." IEEE Electron Device Letters, vol. 13, no. 1. January 1992.
	V	Koh, P. J. et al. "Millimeter Wave Tripler Evaluation of a Metal/2-DEG Schottky Diode Varactor." IEEE Microwave and Guided Wave Letters, vol. 5, no. 2. March 1995.
	W	Castro, F. et al. "Schottky Contact between Metal and Two-Dimensional Electron Gas: Device Applications to Low-Noise Optical Detectors." IEEE MTT-S IMOC '97 Proceedings. 1997.
	X	Anwar, A. et al. "Barrier Enhancement Mechanisms in Heterodimensional Contacts and their Effect on Current Transport." IEEE Transactions on Microwave Theory and Techniques, vol. 50, no. 1. January 2002.

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

<b>Notice of References Cited</b>	Application/Control No. 10/573,458		Applicant(s)/Patent Under Reexamination OTSUKA ET AL.	
	Examiner Christopher M. Roland		Art Unit 2893	Page 2 of 2

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Daniels, R. et al. "Quantum-Well p-Channel AlGaAs/InGaAs/GaAs Heterostructure Insulated-Gate Field-Effect Transistors with Very High Transconductance." IEEE Electron Device Letters, vol. 9, no. 7. July 1988.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.